Electronic Supplementary Information

Growth of Flexible N-doped SiC Quasialigned Nanoarrays and Their Field Emission Properties

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Table S1. Turn-on and threshold fields[a] for SiC emitters and other nanostructured flexible cathodes

Emitters	Turn-on fields (V/μm)	Threshold fields (V/μm)	Ref.
N-doped nanoporous SiC	4.4 ~ 9.6	--	1
tubular β-SiC	5	10 at 10 mA/cm^2	2
SiC nanowires/nanorods	3.33	5.77 at 10 mA/cm^2	3
hierarchical β-SiC nanoarchitectures	12	--	4
aligned SiC porous nanowires	2.3 ~ 2.9	--	5
Al_2O_3 nanoparticle-decorated tubular SiC	2.4	5.37 at 10 mA/cm^2	6
core-shell SiC-SiO_2 nanowires	3.3 ~ 4.5	--	7
bamboo-like β-SiC nanowires	10.1	--	8
ultrathin 3C-SiC nanobelts	3.2	--	9
β-SiC nanowires	--	4	10
lawn-like SiC nanowires	2.1	--	11
carbon-coated SiC nanowires	4.2	--	12
BN Coated SiC Nanowires	6	20 at 10 mA/cm^2	13
N-doped SiC quasialigned nanoarrays	1.90	2.53	this work
conical nanocarbon	6.1 at 10 nA/cm^2	9.5 at 10 μA/cm^2	14
carbon nanotubes	3.6	--	15
carbon nanofibers	--	~ 3.65 at 1 μA/cm^2	16
tungsten oxide nanowires	--	4.3 at 10 mA/cm^2	17
CdS nanowire array	--	10.57 ~ 12.7	18
vertical ZnO nanowires/graphene hybrids	2.0 ~ 2.8	--	19
multiwall carbon nanotubes	2.05 at 1 μA/cm^2	2.2 at 10 μA/cm^2	20

[a] The turn-on and threshold fields required to generate an emission current density of 10 μA/cm^2 and 1 mA/cm^2, respectively. If other values are used, it will be mentioned separately.

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